

irradiating said semiconductor film by scanning with at least two pairs of linear infrared lights in a predetermined direction,

wherein at least two of said linear infrared lights are located over said substrate and the other at least two of said linear infrared lights are located at a backside of said substrate.

20. (Amended) A method for manufacturing semiconductor device comprising the steps of:

forming an amorphous semiconductor film over a substrate; and

crystallizing the semiconductor film by scanning with at least two pairs of upper and lower linear infrared lights in a predetermined direction,

wherein said at least two upper linear infrared light are located over said substrate and said at least two lower linear infrared light are located at a backside of said substrate, and wherein said predetermined direction is consistent with a direction of crystal growth in the semiconductor film.

21. (Amended) A method for manufacturing semiconductor

forming an amorphous semiconductor film over a substrate; and

crystallizing the semiconductor film by scanning the semiconductor film with at least two pairs of upper and lower linear infrared lights in a direction in order to form and move a temperature gradient the semiconductor film,

wherein said at least two upper linear infrared light are located over said semiconductor film and said at least two lower linear infrared light are located at an underside of said semiconductor film, and

wherein said direction is coincident with a direction of crystal growth to be proceeded in the semiconductor film.

36. (Amended) A method for manufacturing a semiconductor

device comprising steps of:

forming an amorphous semiconductor film over a substrate; and

crystallizing said semiconductor film by irradiating said semiconductor film with at least two kinds of linear infrared lights while in vacuum and irradiating a prepolymer at the linear infrared lights,

wherein at least two of said linear integrated lights are

linear infrared lights are located at a backside of said substrate, and

wherein an irradiating direction is coincident with a direction of crystal growth to be proceeded in the semiconductor film.

REMARKS

Reconsideration and allowance of the above-referenced application are respectfully requested.

Independent claims 2, 20, 29, and 36 are amended herewith to emphasize the feature that the semiconductor film is irradiated by scanning using at least two pairs of linear infrared lights in a predetermined direction. At least two of the linear infrared lights are located over the substrate, and the other two are located at a backside of the substrate. This feature is shown in FIG. 6.

None of the previously applied rejections is in any way suggestive of this feature. Therefore, for all of these reasons, it is respectfully suggested that this obviates the rejections.

In view of the above amendment and remarks, therefore, all of the claims should be in condition for allowance. A formal notice to that effect is respectfully solicited.